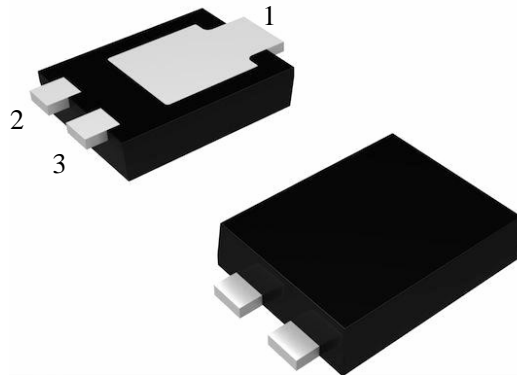
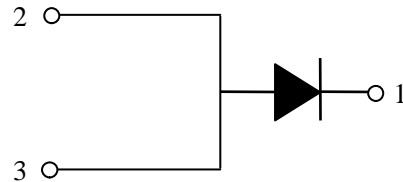


45V Trench MOS Barrier Schottky Low VF 0.46V@10A, 25 °C

Features

- Trench MOS schottky technology
- Low stored charge Majority Carrier Conduction
- Ultra low forward voltage drop
- Low leakage current
- Low power loss and high efficiency
- High surge capacity
- ESD rating:>20K volts

10 Amperes, 45 Volts



Typical Application

Schottky rectifier design for high frequency switched mode power supplies, such as adaptators and on board DC/DC converters.

TO-277

Device Summary

Symbol	Value
$I_F(AV)$	10A
V_{RRM}	45V
$V_F(Typical)$	0.46V
$T_j(max)$	150 °C

Mechanical Data

Case: JEDEC TO-277, molded plastic

Terminals: Plated leads, solderable per

MIL-STD-750, Method 2026

Mounting Position: Any

Note: Pins 2 & 3 must be electrically connected at the printed circuit board.

Major Rating and Characteristics

Symbol	Parameter		Values	Units
V_{RRM}	Repetitive peak reverse voltage		45	V
T_J	Storage temperature range		-55 to 150	$^{\circ}\text{C}$
I_{FSM}	Surge non repetitive forward current	10 ms sine or 6 ms rect. pulse	150	A
$I_{F(AV)}$	Maximum average forward current 50 % duty cycle, rectangular waveform		$T_c=35^{\circ}\text{C}$ 10	

Electrical Characteristics($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Test condition		Symbol	TYP	MAX	UNITS
Forward Voltage drop	$I_F=2\text{A}$	$T_A=25^{\circ}\text{C}$	$V_F^{(1)}$	0.35	-	V
	$I_F=5\text{A}$			0.42		
	$I_F=10\text{A}$			0.46	0.51	
	$I_F=2\text{A}$	$T_A=125^{\circ}\text{C}$		0.30	-	
	$I_F=5\text{A}$			0.36		
	$I_F=10\text{A}$			0.40	0.48	
Reverse leakage current	$V_R=45\text{V}$	$T_A=25^{\circ}\text{C}$	$I_R^{(2)}$	20	100	μA
		$T_A=125^{\circ}\text{C}$		13	70	mA
Junction capacitance	$V_R=5\text{V}_{DC}, 25^{\circ}\text{C}(1\text{MHz})$		C_j	-		pF

Notes (1) Pulse test: 300us pulse width,2% duty cycle (2) Pulse test: 300us pulse width,2% duty cycle

Thermal Characteristics($T_A=25^{\circ}\text{C}$ unless otherwise noted)

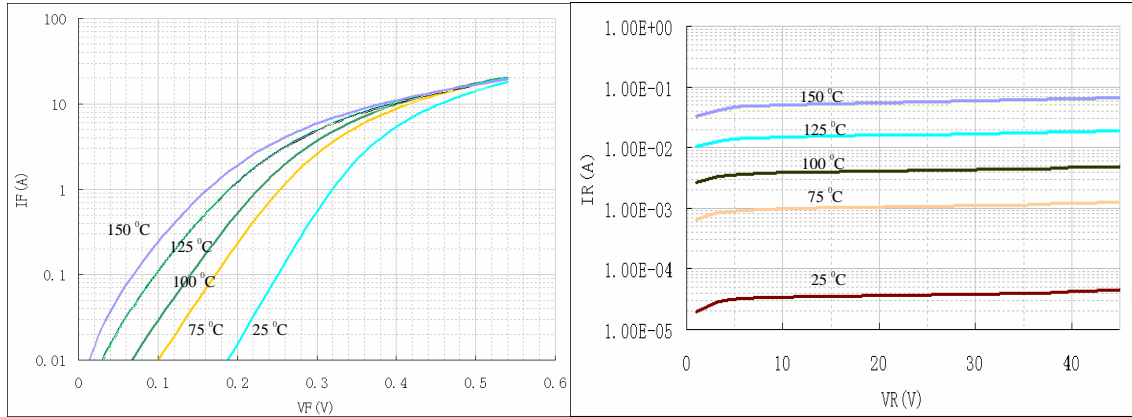
Parameter	Symbol	SK10U45LA	UNIT
Typical thermal resistance	$R_{JA}^{(1)}$	75	$^{\circ}\text{C}/\text{W}$
	$R_{JM}^{(2)}$	34	

Notes (1) Free air, mounted on recommended PCB, 2oz.pad area; thermal resistance R_{JA} -junction to ambient
 (2) Cathode pad dimensions 18.8mm x 14.4mm. Anode pad dimensions 5.6mm x 14.4mm;
 R_{JM} -junction to mount

Characteristics Curves ($T_A=25\text{ }^\circ\text{C}$ unless otherwise noted)

Fig.1 Typical Forward Voltage Characteristics

Fig.2 Typical Reverse Leakage Characteristics



Package Outline Dimensions in Millimeters

